Am8216 • Am82

Four-Bit Parallel Bidirectional Bus Driver

Distinctive Characteristics

- Data bus buffer driver for 8080 type CPU's
- Low input load current 0.25mA maximum
- High output drive capability for driving system data bus -50mA at 0.5V
- Am8216 has non-inverting outputs
- Output high voltage compatible with direct interface to MOS
- Three-state outputs
- Advanced Schottky processing
- Available in military and commercial temperature
- Am8226 has inverting outputs

FUNCTIONAL DESCRIPTION

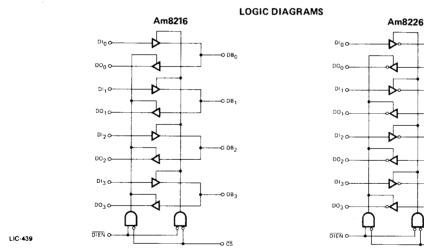
The Am8216 and Am8226 are four-bit, bi-directional bus drivers for use in bus oriented applications. The non-inverting Am8216, and inverting Am8226 drivers are provided for flexibility in system design.

Each buffered line of the four bit driver consists of two separate buffers that are three-state to achieve direct bus interface and bi-directional capability. On one side of the driver the output of one buffer and the input of another are tied together (DB), this side is used to interface to the system side components such as memories, 1/O, etc., because its interface is TTL compatible and it has high drive (50mA). On the other side of the driver the inputs and outputs are separated to provide maximum flexibility. Of course, they can be tied together so that the driver can be used to buffer a true bi-direc-

tional bus. The DO outputs on this side of the driver have a special high voltage output drive capability so that direct interface to the 8080 type CPUs is achieved with an adequate amount of noise immunity.

The CS input is a device enable. When it is "high" the output drivers are all forced to their high-impedance state. When it is a "LOW" the device is enabled and the direction of the data flow is determined by the DIEN input.

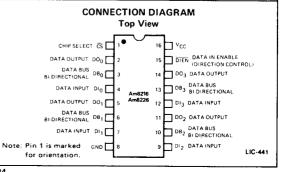
The DIEN input controls the direction of data flow which is accomplished by forcing one of the pair of buffers into its high impedance state and allowing the other to transmit its data. A simple two gate circuit is used for this function.



	A1110220	
0100	D	٦
DO ₀ o	\neg	O DB _O
DI10		О DВ,
DO ₁ O-	→	J
DI ₂ O		O D82
DO ₂ O	-	
0130	>	OD83.
0030		
DIEN		o cs

Package Type	Temperature Range	Am8216 Order Number	Am8226 Order Number
Hermetic DIP	-55°C to +125°C	MD8216	MD8226
Hermetic DIP	0°C to +70°C	D8216	D8226
Molded DIP	0°C to +70°C	P8216	P8226
Dice	0°C to +70°C	AM8216XC	AM8226XC

ORDERING INFORMATION



LIC-440

MAXIMUM RATINGS (Above which the useful life may be impaired)

Temperature (Ambient) Under Bias	-55°C to +125°C
Storage Temperature	-65°C to +150°C
All Output and Supply Voltages	-0.5 V to +7.0 V
All Input Voltages	-1.0 V to +5.5 V
Output Currents	125 mA

Am8216 AND Am8226 MILITARY

ELECTRICAL CHARACTERISTICS OVER OPERATING TEMPERATURE RANGE (-55°C to +125°C)

The following conditions apply unless otherwise specified:

MD8216, MD8226 (MIL) $T_A = -55^{\circ}C \text{ to } +125^{\circ}C$ $V_{CC} = 5.0V \pm 10\%$

DC CHARACTERISTICS

Parameters	Description		Test Conditions		Min.	Typ. (Note 1)	Max.	Units
I _{F1}	Input Load Current DIEN, CS		V _F = 0.45			-0.15	0.5	mA
I _{F2}	Input Load Current All Other In	puts	V _F = 0.45			0.08	-0.25	mA
I _{R1}	Input Leakage Current DIEN, C	S	V _R = 5.5V				80	μА
I _{R2}	Input Leakage Current DI Input	is .	V _R = 5.5V				40	μА
v _C	Input Forward Voltage Clamp		I _C = -5.0mA				-1.2	Volts
VIL	Input LOW Voltage	Am8216					0.95	Volts
*1L	The Low Voltage	Am8226					0.9	Volts
v _{IH}	Input HIGH Voltage				2:0			Volts
10	Output Leakage Current	DO					20	
•0	(Three-State)	DB	V _O = 0.45V/5.5V		·		100	μΑ
Icc	Power Supply Current	Am8216				95	130	
	Tower supply current	Am8226				85	120	mA
V _{OL1}	Output LOW Voltage		DO Outputs I _{OL} = 15mA DB Outputs I _{OL} = 25mA			0.3	0.45	Volts
V _{OL2}	Output LOW Voltage		DB Outputs IOL = 45mA			0.5	0.6	Volts
V _{OH1}	Output HIGH Voltage		I _{OH} = -0.5mA		3.4	4.0		
VOH1	Output man voltage		DO Outputs IOH = -2.0mA		2.4			Volts
v _{OH2}	Output HIGH Voltage		DB Outputs I _{OH} = -5.0mA		2.4	3.0		Volts
los	Output Short Circuit Current		DO Outputs ≈ 0V, V _{CC} =	5.0V	-15	-35	-65	
.03	Salpar Griori Gricuit Gurient		DB Outputs = 0V, V _{CC} =	5.0V	-30	-75	-120	mΑ

AC CHARACTERISTICS OVER OPERATING TEMPERATURE RANGE (-55°C to +125°C)

Parameters	Description		Test Conditions	Min.	Typ. (Note 1)	Max.	Units
tPD1	Input to Output Delay DO Outputs		$C_L = 30pF, R_1 = 300\Omega, R_2 = 600\Omega$		15	25	ns
tPD2	Input to Output Delay DB Outputs	Am8216	C = 200=5 B = 000 B = 1200		20	33	
1702		Am8226	$C_L = 300 pF, R_1 = 90\Omega, R_2 = 180\Omega$		16	25	ns
tr	Output Enable Time	Am8216	Note 2		45	75	
	Salpar Endolo (IIIIe	Am8226	Note 3		35	62	ns
	Output Disable Time	Am8216	N		20	40	
t _D	Output Disable Time	Am8226	Note 4		16	38	ns

Am8216 · Am8226

Am8216 AND Am8226 COMMERCIAL

ELECTRICAL CHARACTERISTICS OVER OPERATING TEMPERATURE RANGE (0°C to +70°C)

The following conditions apply unless otherwise specified:

D8216, D8226, P8216, P8226 (COM'L)

 $T_A = 0^{\circ} C \text{ to } +70^{\circ} C$ $V_{CC} = 5.0 V + 5\%$

DC CHARACTERISTICS

Parameters	Descrip	tion	Test Conditions	Min.	Typ. (Note 1)	Max.	Units
I _{F1}	Input Load Current DIEN, CS		V _F = 0.45		-0.15	-0.5	mA
IF2	Input Load Current All Other In	nputs	V _F = 0.45		-0.08	-0.25	mA
I _{R1}	Input Leakage Current DIEN, C	ŝ	V _R = 5.25V			20	μА
I _{R2}	Input Leakage Current DI Input	ts	V _R = 5.25V		-	10	μА
v _C	Input Forward Voltage Clamp		I _C = -5.0mA		+	-1.0	Volts
VIL	Input LOW Voltage				 	0.95	Volts
VIH	Input HIGH Voltage			2.0	 		Volts
Pol	Output Leakge Current	DO	V _O = 0.45V/5.5V			20	Voits
1.01	(Three-State)	DB				100	μA
Icc	Power Supply Current	Am8216			95	130	ļ
•00	Tower Supply Current	Am8226			85	120	mA
V _{OL1}	Output LOW Voltage		DB Outputs IOL = 15mA DB Outputs IOL = 25mA		0.3	0.45	Volts
V _{OL2}	Output LOW Voltage	Am8216	DB Outputs IOL = 55mA		0.5	0.6	
*OL2		Am8226	DB Outputs IOL = 50mA		0.5	0.6	Volts
V _{OH1}	Output HIGH Voltage		DO Outputs IOH =1.0mA COM'L	3.65	4.0		Volts
V _{OH2}	Output HIGH Voltage	,	DB Outputs I _{OH} = -10mA	2.4	3.0		Volts
los	Output Short Circuit Current		DO Outputs ≅ 0V	-15	-35	-65	
-03	Salpar Short Should Carrent		DB Outputs V _{CC} = 5.0V	-30	-75	-120	mA

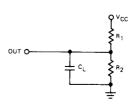
AC CHARACTERISTICS OVER OPERATING TEMPERATURE RANGE (0°C to +70°C)

Parameters	Description Test Conditions		Min.	Typ. (Note 1)	Max.	Units	
tPD1	Input to Output Delay DO Outputs		$C_L = 30pF, R_1 = 300\Omega, R_2 = 600\Omega$		15	25	ns
tPD2	Input to Output Delay DB Outputs	Am8216	C = 200. F B = 200. B = 400.		20	30	
102	——————————————————————————————————————	Am8226	$C_L = 300 \text{pF}, R_1 = 90 \Omega, R_2 = 180 \Omega$		16	25	ns
tE	Output Enable Time	Am8216	Note 2		45	65	
		Am8226	Note 3	-	35	54	ns
t _D	Output Disable Time		Note 4		20	35	ns

TEST CONDITIONS

TEST LOAD CIRCUIT

Input pulse amplitude of 2.5 V. Input rise and fall times of 5.0 ns between 1.0 and 2.0 volts. Output loading is 5.0 mA and 10 pF. Speed measurements are made at 1.5V levels.



CAPACITANCE	(Note	5)
Parameters		Descript

CAPACITANC	E (Note 5)		B.4:	(No. 1)	Max.	Units
Parameters	Description	Test Conditions	Min.	(Note 1)	8.0	pF
CIN	Input Capacitance	VBIAS = 2.5V, VCC = 5.0V		+		
COUT1	Output Capacitance	TA = 25°C, f = 1.0MHz		6.0	10	pF
COLITS	Output Capacitance			13	18	pF

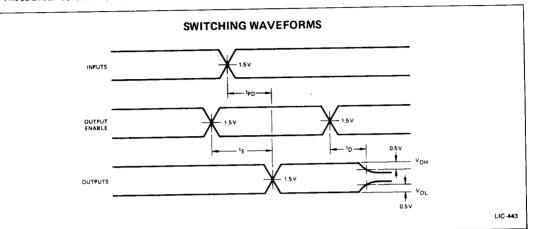
- Notes: 1. Typical values are for T_A = 25°C, V_{CC} = 5.0 V.

 2. DO outputs, C_L = 30pF, R₁ = 300/10kΩ, R₂ = 180/1.0kΩ; DB outputs, C_L = 300 pF, R₁ = 90/10kΩ, R₂ = 180/1.0kΩ.

 3. DO outputs, C_L = 30pF, R₁ = 300/10kΩ, R₂ = 600/1.0kΩ; DB outputs, C_L = 300pF, R₁ = 90/10kΩ, R₂ = 180/1.0kΩ.

 4. DO outputs, C_L = 5.0pF, R₁ = 300/10kΩ, R₂ = 600/1.0kΩ; DB outputs, C_L = 5.0pF, R₁ = 90/10kΩ, R₂ = 180/1.0kΩ.

 - 5. This parameter is periodically sampled and not 100% tested.



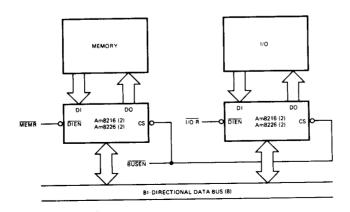
FUNCTION TABLE

			8216			26
DIEN	CS		DB	DO	DB	DO
L	L	DI → DB	DI	z	DĪ	z
Н -	L	DB ⇒ DO	Z	DB	Z	DB
	Н		Z	Z	Z	z
Н —	Н	i	z	Z	Z	Z

H = HIGH L = LOW

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TYPICAL APPLICATION

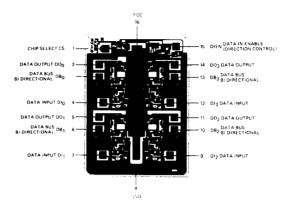


MEMORY AND I/O INTERFACE TO A BI-DIRECTIONAL BUS

LIC-445

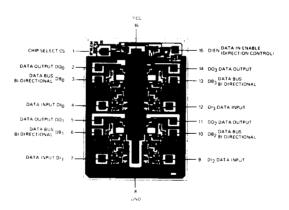
Metallization and Pad Layout

Am8216



DIE SIZE 0.066" X 0.090"

Am8226



DIE SIZE 0.066" X 0.090"